

### **AMENDMENT TO THE ABSTRACT**

The following abstract will replace all prior versions of the abstract in the application:

#### **ABSTRACT**

A device for carrying out a plasma enhanced process, ~~in particular a plasma enhanced chemical vapour deposition process,~~ includes, ~~comprises~~ within a vacuum chamber, at least one magnetron electrode (32) constituting an unbalanced magnetron having a flat magnetron face (20) with peripheral and central magnetic poles of opposite polarities ~~and being connected to a source (34) of an alternating voltage.~~ The device further ~~comprises means~~ includes a device for positioning a substrate (25), the substrate having ~~with a~~ surface to be treated facing the magnetron face (20), and a gas supply means ~~device~~ for supplying a process gas or process gas mixture to the space between the magnetron face (20) and the treated ~~surface to be treated.~~ ~~For achieving an optimum deposition rate, the~~ The distance between the magnetron face (20) and the treated ~~surface to be treated~~ is adapted to the magnetic field created by the magnetron electrode (32) such that there is a visible plasma band running between darker tunnels formed by magnetic field lines extending between peripheral and central magnetic poles of the magnetron face (20) and the treated ~~surface to be treated~~, the plasma band having a minimum width but having homogeneous brightness towards the treated ~~surface to be coated~~ a ~~homogeneous brightness.~~ The distance between the ~~surface to be treated~~ and the magnetron face is preferably between 2 and 20% larger than the height of the tunnels. The device is applicable e.g. for coating a web of a polymer film material with silicon oxide in order to improve its barrier properties.

(Figure 3)